

N-channel 80 V,15 mΩ logic level MOSFET in LFPAK56

11 November 2014

Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	62	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	147	W
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	12.2	15	mΩ
Dynamic char	acteristics					
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 15 A; V _{DS} = 64 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	8.7	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UT 4
4	G	gate	មុច្ចថ្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Fable 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9Y14-80E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y14-80E	91480E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; \ Pulsed$	[1][<u>2]</u>	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	147	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	62	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	44	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	250	А

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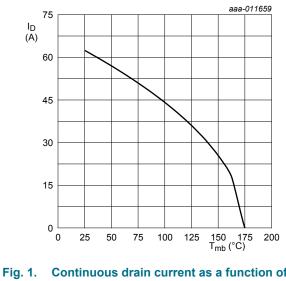
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
I _S	source current	T _{mb} = 25 °C		-	62	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	250	А
Avalanche i	ruggedness	,				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 62 \; {\sf A}; {\sf V}_{\sf sup} \le 80 \; {\sf V}; {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 5 \; {\sf V}; \; {\sf T}_{\sf j(init)} = 25 \; {}^\circ{\sf C}; \; {\sf unclamped}; \\ & {\sf Fig. \; 3} \end{split}$	[3][4]	-	79.6	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_{j}$ and or $\rm V_{GS}$ [1]
- [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information. [4]





 $V_{GS} \ge 5V$

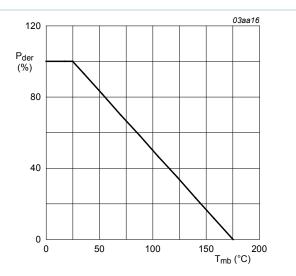
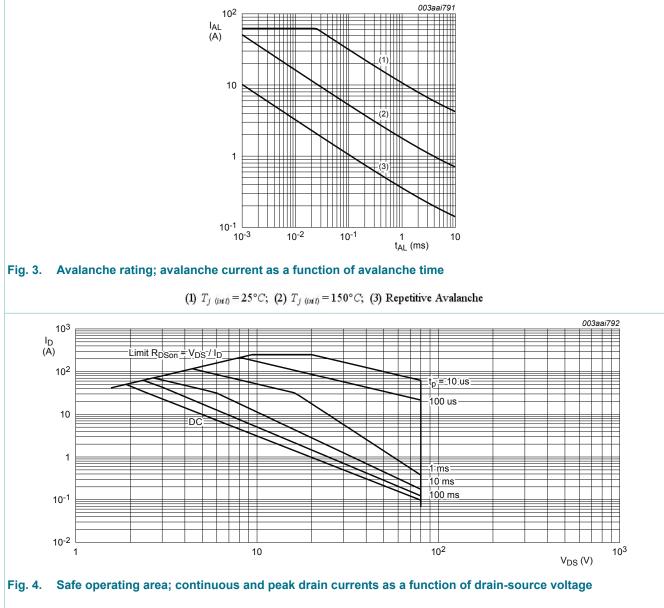


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$

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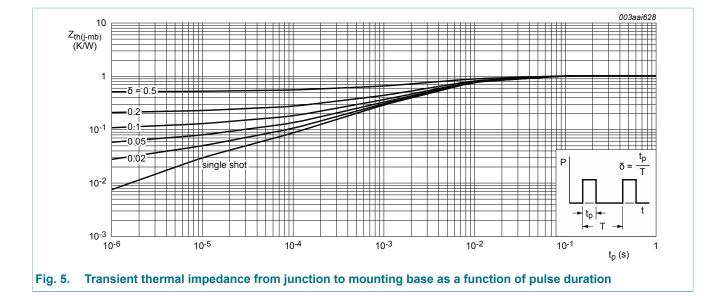


 $T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.02	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 9	-	-	2.45	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 9	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.25	10	μA
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	12.2	15	mΩ
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	11.3	14	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	37.65	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics	· · · · · · · · · · · · · · · · · · ·	I			_
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 64 V; V _{GS} = 5 V;	-	28.9	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	8.1	-	nC
Q _{GD}	gate-drain charge		-	8.7	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	3479	4640	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	236	283	pF
C _{rss}	reverse transfer capacitance		-	114	156	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 4 Ω; V _{GS} = 5 V;	-	15.3	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	24.6	-	ns
t _{d(off)}	turn-off delay time		-	45.3	-	ns
t _f	fall time		-	24.7	-	ns
Source-dra	in diode	· · · · · · · · · · · · · · · · · · ·	1			
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;	-	25.8	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	29.3	-	nC

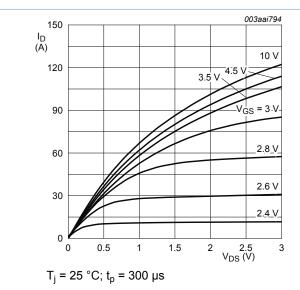


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

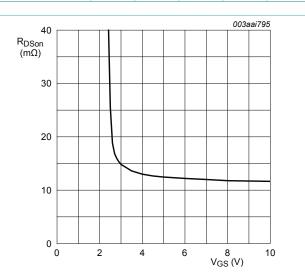
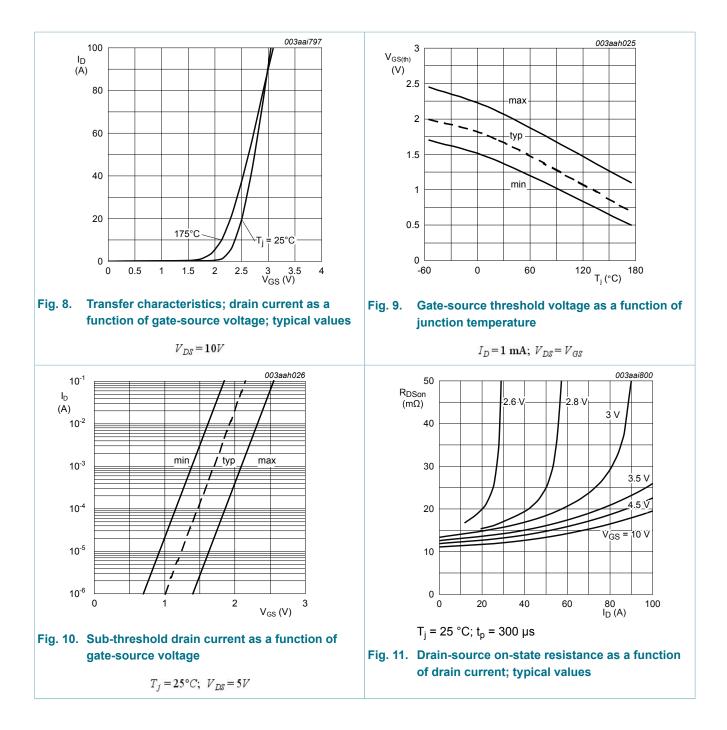


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 15A$

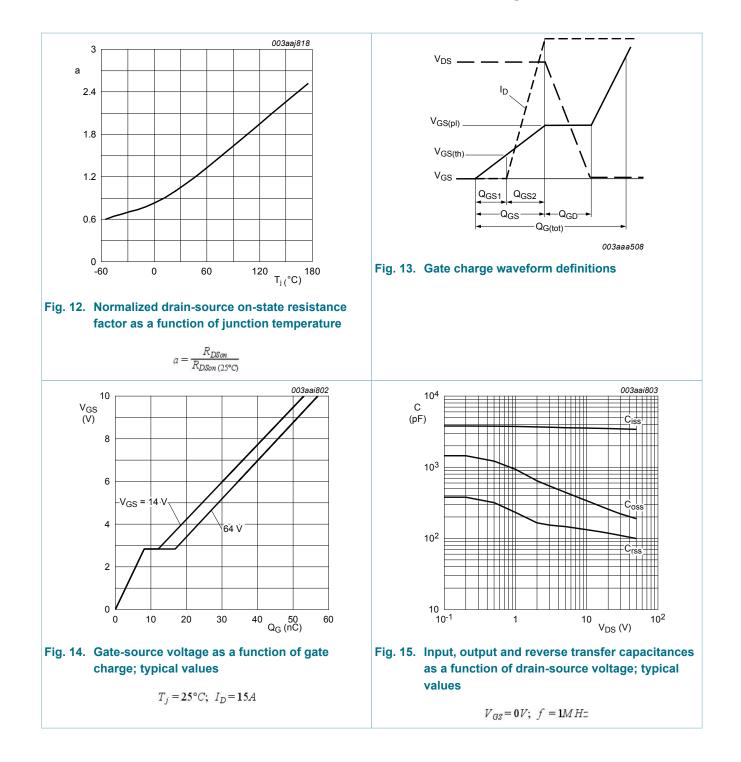
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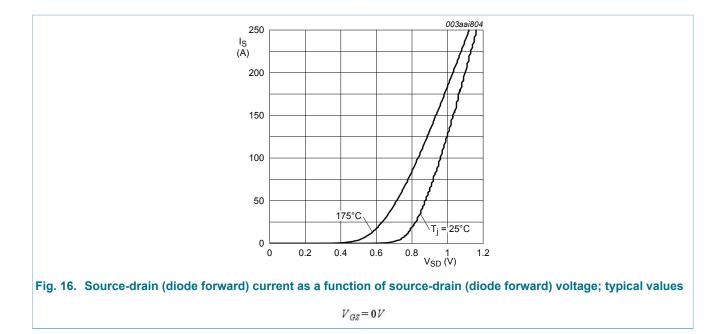
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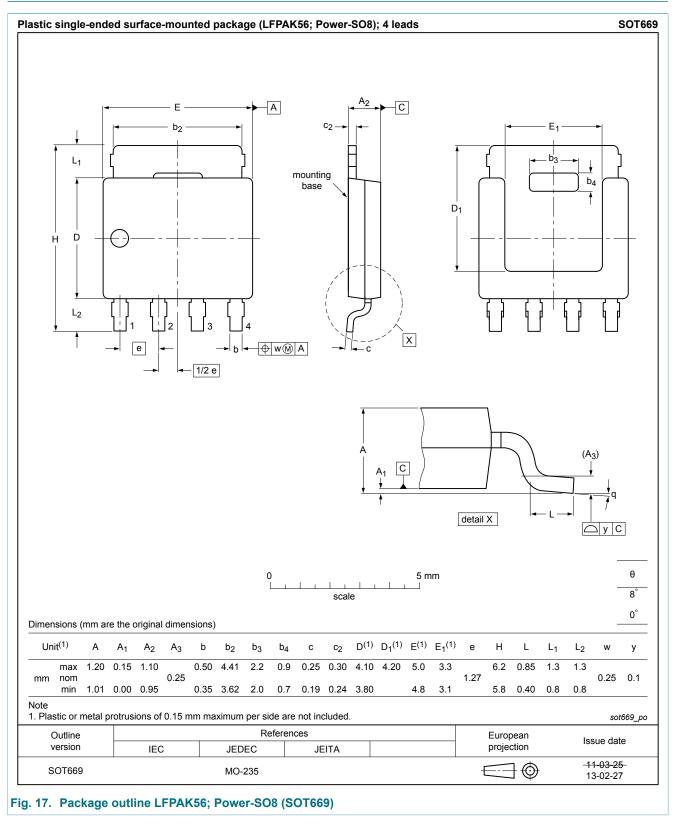
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11. Package outline



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Product [short] data sheet	Production	This document contains the product specification.

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